

19 April 2003

09/744,465

L Number	Hits	Search Text	DB	Time stamp
-	79	205/\$.ccls. and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/16 08:33
-	263	205/\$.ccls. and (polysilicon or ((polycrystalline or amorphous) adj silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/16 11:06
-	6	(205/\$.ccls. and (polysilicon or ((polycrystalline or amorphous) adj silicon))) and dicing	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/15 16:19
-	10	(205/\$.ccls. and (polysilicon or ((polycrystalline or amorphous) adj silicon))) and (dicing or dice or diced)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/15 16:26
-	268	205/\$.ccls. and (polysilicon or ((polycrystalline or amorphous) adj silicon) or "poly-silicon" or "poly-crystalline silicon" or "polycrystal silicon" or "poly-crystal silicon")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/15 16:26
-	10	(205/\$.ccls. and (polysilicon or ((polycrystalline or amorphous) adj silicon) or "poly-silicon" or "poly-crystalline silicon" or "polycrystal silicon" or "poly-crystal silicon")) and (dicing or dice or diced)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/15 16:27
-	10	(205/\$.ccls. and (polysilicon or ((polycrystalline or amorphous) adj silicon))) and (die)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/15 16:27
-	11	205/\$.ccls. and ((polysilicon or ((polycrystalline or amorphous) adj silicon)) near2 (connector or conductor or connecting or interconnect or connected))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/16 11:14
-	78	205/\$.ccls. and (wafer or semiconductor) and ((back or rear) near contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/16 15:35
-	1690	205/118,123,133,157,205,220.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/16 15:35
-	117	(205/118,123,133,157,205,220.ccls. and (semiconductor or wafer)) and seal	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/16 15:36
-	126	205/118,123,133,157,205,220.ccls. and (conductive near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/16 15:37
-	11	((205/118,123,133,157,205,220.ccls. and (semiconductor or wafer)) and seal) and (205/118,123,133,157,205,220.ccls. and (conductive near substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/16 15:38

-	646	205/118,123,133,157,205,220.ccls. and (s miconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:43
-	262	205/118,123,133,157,205,220.ccls. and ((semiconductor or wafer) with (silicon or polysilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:27
-	102	(205/118,123,133,157,205,220.ccls. and ((semiconductor or wafer) with (silicon or polysilicon))) and ((type with silicon) or (conduct\$3 near substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:27
-	74	(205/118,123,133,157,205,220.ccls. and ((semiconductor or wafer) with (silicon or polysilicon))) and ((type near silicon) or (conduct\$3 near substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:27
-	68	((205/118,123,133,157,205,220.ccls. and ((semiconductor or wafer) with (silicon or polysilicon))) and ((type near silicon) or (conduct\$3 near substrate))) and (plat\$3 or electroplat\$3 or electrodeposit\$3 or electrochem\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:32
-	42	((((205/118,123,133,157,205,220.ccls. and ((semiconductor or wafer) with (silicon or polysilicon))) and ((type near silicon) or (conduct\$3 near substrate))) and (plat\$3 or electroplat\$3 or electrodeposit\$3 or electrochem\$6)) and (seed or plating)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:33
-	11	((((205/118,123,133,157,205,220.ccls. and ((semiconductor or wafer) with (silicon or polysilicon))) and ((type near silicon) or (conduct\$3 near substrate))) and (plat\$3 or electroplat\$3 or electrodeposit\$3 or electrochem\$6)) and (seed)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:33
-	1690	205/118,123,133,157,205,220.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:43
-	64	205/118,123,133,157,205,220.ccls. and ((silicon or polysilicon) near2 (contact or conductor or connecting or connector or connected or connect or bridge or bridged or joined or conductive or conducting or bridging or contacted or contacting or linking or linked or link or linkage or join or joining))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:51
-	66	205/118,123,133,157,205,220.ccls. and ((silicon or polysilicon) near2 (contact or conductor or connecting or connector or connected or connect or bridge or bridged or joined or conductive or conducting or bridging or contacted or contacting or linking or linked or link or linkage or join or joining or interconnect or interconnecting or interconnected))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 11:52

-	41	(205/118,123,133,157,205,220.ccls. and ((silicon or polysilicon) near2 (contact or conductor or connecting or connector or connected or connect or bridg or bridged or join d or conductive or conducting or bridging or contacted or contacting or linking or linked or link or linkage or join or joining or interconnect or interconnecting or interconnected))) not (silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 12:36
-	2	5483741.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 11:00
-	108	205/118,123,133,157,205,220.ccls. and (dice or diced or dicing or die)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 12:46
-	55	(205/118,123,133,157,205,220.ccls. and (dice or diced or dicing or die)) and (silicon or polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 12:47
-	83309	204/\$.ccls. or 205/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 09:10
-	471	(204/\$.ccls. or 205/\$.ccls.) and seal and contact and finger	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 09:10
-	190	((204/\$.ccls. or 205/\$.ccls.) and seal and contact and finger) and (wafer or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 09:11
-	87	((((204/\$.ccls. or 205/\$.ccls.) and seal and contact and finger) and (wafer or semiconductor)) and (electroplate or electroplating or plating or electroplated)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 09:12
-	0	205/\$.ccls. and ((silicon or polysilicon) near3 bus)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 10:18
-	8	205/\$.ccls. and ((silicon or polysilicon) with (bus or busbar))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 10:21
-	51	438/\$.ccls. and ((silicon or polysilicon) near3 (bus or busbar))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 10:25
-	19	438/\$.ccls. and ((silicon or polysilicon) near (bus or busbar))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 10:25

	89	205/\$.ccls. and (dice or diced or dicing)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 11:01
	84	(205/\$.ccls. and (dice or diced or dicing)) and (semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 11:06
	0	jp-090055398-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 11:07
	2	jp-09055398-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 11:44
	20	205/118,123,133,157,205,220.ccls. and (scribe or scribing or scribed)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 11:44
	23	(US-6132585-\$. or US-5643803-\$. or US-5393399-\$. or US-5275715-\$. or US-6521118-\$. or US-5730852-\$. or US-4227291-\$. or US-5421987-\$. or US-6258240-\$. or US-5726075-\$. or US-4759830-\$. or US-4681656-\$. or US-5483741-\$. or US-5000827-\$. or US-6027630-\$. or US-3625837-\$.).did. or (US-20030059929-\$. or US-20020084192-\$. or US-20020008037-\$. or US-20020008034-\$. or US-20010032787-\$. or US-20020157958-\$.).did. or (JP-09055398-\$.).did.	USPAT; US-PGPUB; JPO	2003/05/19 12:10
	8	((US-6132585-\$. or US-5643803-\$. or US-5393399-\$. or US-5275715-\$. or US-6521118-\$. or US-5730852-\$. or US-4227291-\$. or US-5421987-\$. or US-6258240-\$. or US-5726075-\$. or US-4759830-\$. or US-4681656-\$. or US-5483741-\$. or US-5000827-\$. or US-6027630-\$. or US-3625837-\$.).did. or (US-20030059929-\$. or US-20020084192-\$. or US-20020008037-\$. or US-20020008034-\$. or US-20010032787-\$. or US-20020157958-\$.).did. or (JP-09055398-\$.).did.) and (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 12:19
	802	438/460,462.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 12:20
	3	438/460,462.ccls. and ((silicon or polysilicon) near (bus or busbar or interconnect or connector or conductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 12:27
	11	438/460,462.ccls. and ((silicon or polysilicon) near2 (bus or busbar or interconnect or connector or conductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 12:42

-	4240	428/901,545.ccls. or 439/55,78.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 12:42
-	12	(428/901,545.ccls. or 439/55,78.ccls.) and ((silicon or polysilicon) near2 (conductor or bus or busbar or int rconnect or connector))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 13:36
-	2	("4939568").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 13:37
-	0	ep-0780890-a1-did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 13:37
-	0	ep-780890-a1-did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 13:37
-	0	ep-0780890-a1.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 13:38
-	2	ep-780890-a1.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 13:38
-	0	de-2830761-a1.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 13:39
-	0	de-02830761-a1.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 13:39
-	0	de-002830761-a1.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 13:39